



瑞而美 **work steadily**

蘇州瑞而美光電科技有限公司

Suzhou Realmay Lightings Tech Co., Ltd

Specification of 4" Si Polished Wafer

Item	Specification	Unit
Crystal Growth Method	FZ	--
Conductivity Type	--	--
Dopant	--	--
Crystal Orientation	$\langle 111 \rangle \pm 1$	degree
Off Orientation	0 ± 1	degree
Resistivity	> 1500	$\Omega\text{-cm}$
EPD	< 100	ea/cm ²
Oxygen Contents	$\sim 1 \times E16 \text{ at/cm}^3$	--
Carbon Contents	$< 2 \times E16 \text{ at/cm}^3$	--
Diameter	100 ± 0.5	mm
Primary Flat Location	$\langle 110 \rangle \pm 1$	degree
Primary Flat Length	32.5 ± 2.5	mm
Secondary Flat Location	--	degree
Secondary Flat Length	--	mm
Edge Profile-Type/Angle	R-type	--
Thickness	300 ± 25	um
TTV	≤ 10	um
Bow	≤ 35	um
Warp	≤ 35	um
Front Surface	Polished	--
Back Surface	Etched	--
Appearance	Free from cracks, crow's feet, saw marks, scratches and stains	
Packing	5pcs/box (Entergris Box)	
Note	--	

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